

Semiconductor Physics And Devices 3th Third Edition Text Only

Preface -- 1. Introduction to Plastics and Polymers -- 2. Chapter 2 - Introduction to the Mechanical, Thermal and Permeation Properties of Plastics and Elastomers -- 3. Production of films -- 4. Markets and Applications for films -- 5. Styrenic Plastics -- 6. Polyesters -- 8. Polyamides (Nylons) -- 9. Polyolefins -- 10. Polyvinyls & Acrylics -- 11. Fluoropolymers -- 12. High Temperature/High Performance Polymers -- 13. Elastomers and rubbers -- 14. Renewable Resource or biodegradable polymers -- Appendices -- Permeation Unit Conversion Factors -- Vapor Transmission rate Conversion factors.

Resistivity -- Carrier and doping density -- Contact resistance and Schottky barriers -- Series resistance, channel length and width, and threshold voltage -- Defects -- Oxide and interface trapped charges, oxide thickness -- Carrier lifetimes -- Mobility -- Charge-based and probe characterization -- Optical characterization -- Chemical and physical characterization -- Reliability and failure analysis.

An up-to-date, practical guide on upgrading from silicon to GaN, and how to use GaN transistors in power conversion systems design This updated, third edition of a popular book on GaN transistors for efficient power conversion has been substantially expanded to keep students and practicing power conversion engineers ahead of the learning curve in GaN technology advancements. Acknowledging that GaN transistors are not one-to-one replacements for the current MOSFET technology, this book serves as a practical guide for understanding basic GaN transistor construction, characteristics, and applications. Included are discussions on the fundamental physics of these power semiconductors, layout, and other circuit design considerations, as well as specific application examples demonstrating design techniques when employing GaN devices. GaN Transistors for Efficient Power Conversion, 3rd Edition brings key updates to the chapters of Driving GaN Transistors; Modeling, Simulation, and Measurement of GaN Transistors; DC-DC Power Fundation; Envelope Tracking; and Highly Resonant Wireless Energy Transfer. It also offers new chapters on Thermal Management, Multilevel Converters, and Lidar, and revises many others throughout. Written by leaders in the power semiconductor field and industry pioneers in GaN power transistor technology and applications Updated with 35% new material, including three new chapters on Thermal Management, Multilevel Converters, Wireless Power, and Lidar Features practical guidance on formulating specific circuit designs when constructing power conversion systems using GaN transistors A valuable resource for professional engineers, systems designers, and electrical engineering students who need to fully understand the state-of-the-art GaN Transistors for Efficient Power Conversion, 3rd Edition is an essential learning tool and reference guide that enables power conversion engineers to design energy-efficient, smaller, and more cost-effective products using GaN transistors.

The purpose of this book is to provide the reader with a self-contained treatment of fundamen tal solid state and semiconductor device physics. The material presented in the text is based upon the lecture notes of a one-year graduate course sequence taught by this author for many years in the Department of Electrical Engineering of the University of Florida. It is intended as an introductory textbook for graduate students in electrical engineering. However, many students from other disciplines and backgrounds such as chemical engineering, materials science, and physics have also taken this course sequence, and will be interested in the material presented herein. This book may also serve as a general reference for device engineers in the semiconductor industry. The present volume covers a wide variety of topics on basic solid state physics and physical principles of various semiconductor devices. The main subjects covered include crystal structures, lattice dynamics, semiconductor statistics, energy band theory, excess carrier phenomena and recombination mechanisms, carrier transport and scattering mechanisms, optical properties, photoelectric effects, metal-semiconductor devices, the p–n junction diode, bipolar junction transistor, MOS devices, photonic devices, quantum effect devices, and high speed III-V semiconductor devices. The text presents a unified and balanced treatment of the physics of semiconductor materials and devices. It is intended to provide physicists and mat erials scientists with more device backgrounds, and device engineers with a broader knowledge of fundamental solid state physics.

Semiconductor Devices : Basic Principles

Light-Emitting Diodes

MoS2

Electronic Properties of Materials

Fundamentals of Microelectronics

Learn the basic properties and designs of modern VLSI devices, as well as the factors affecting performance, with this thoroughly updated second edition. The first edition has been widely adopted as a standard textbook in microelectronics in many major US universities and worldwide. The internationally renowned authors highlight the intricate interdependencies and subtle trade-offs between various practically important device parameters, and provide an in-depth discussion of device scaling and scaling limits of CMOS and bipolar devices. Equations and parameters provided are checked continuously against the reality of silicon data, making the book equally useful in practical transistor design and in the classroom. Every chapter has been updated to include the latest developments, such as MOSFET scale length theory, high-field transport model and SiGe-base bipolar devices.

Books are seldom finished. At best, they are abandoned. The second edition of "Electronic Properties of Materials" has been in use now for about seven years. During this time my publisher gave me ample opportunities to update and improve the text whenever the lbook was reprinted. There were about six of these reprinting cycles. Eventually, however, it became clear that substantially more new material had to be added to account for the stormy developments which occurred in the field of electrical, optical, and magneic materials. In particular, expanded sections on flat-panel displays (liquid crystals, electroluminescence devices, field emission displays, and plasma dis. plays) were added. Further, the recent developments in blue- and green emitting LED's and in photonics are included. Magnetic storage devices also underwent rapid development. Thus, magneto-optical memories, magneto resistance devices, and new' magnetic materials needed to be covered. The sections on dielectric properties, ferroelectricity, piezoelectricity, electrostric tion, and thermoelectric properties have been expanded. Of course, the entire text was critically reviewed, updated, and improved. However, the most extensive change I undertook was the conversion of all equations to SI units throughout. In most of the world and in virtually all of the interna tional scientific journals use of this system of units is required. If today's students do not learn to utilize it, another generation is "lost" on this matter. In other words, it is important that students become comfortable with SI units.

This book reviews the structure and electronic, magnetic, and other properties of various MoS2 (Molybdenum disulfide) nanostructures, with coverage of synthesis, Valley polarization, spin physics, and other topics. MoS2 is an important, graphene-like layered nano-material that substantially extends the range of possible nanostructures and devices for nanofabrication. These materials have been widely researched in recent years, and have become an attractive topic for applications such as catalytic materials and devices based on field-effect transistors (FETs) and semiconductors. Chapters from leading scientists worldwide create a bridge between MoS2 nanomaterials and fundamental physics in order to stimulate readers' interest in the potential of these novel materials for device applications. Since MoS2 nanostructures are expected to be increasingly important for future developments in energy and other electronic device applications, this book can be recommended for Physics and Materials Science and Engineering departments and as reference for researchers in the field.

This volume presents a systematic and mathematically accurate description and derivation of transport equations in solid state physics, in particular semiconductor devices.

Film Properties of Plastics and Elastomers

Semiconductors and Electronic Devices

Fundamentals of Modern VLSI Devices

Fundamentals of Silicon Carbide Technology

GaN Transistors for Efficient Power Conversion

This 3e, edited by Peter M. Martin, PNNL 2005 Inventor of the Year, is an extensive update of the many improvements in deposition technologies, mechanisms, and applications. This long-awaited revision includes updated and new chapters on atomic layer deposition, cathodic arc deposition, sculpted thin films, polymer thin films and emerging technologies. Extensive material was added throughout the book, especially in the areas concerned with plasma-assisted vapor deposition processes and metallurgical coating applications. * Explains in depth the many recent i

Provides a basis for understanding the characteristics, operation, and limitations of semiconductor devices. This title deals with the electrical properties and characteristics of semiconductor materials and devices. It intends to bring together quantum mechanics, the quantum theory of solids, and semiconductor material physics.

Dr. Khan's classic textbook on radiation oncology physics is now in its thoroughly revised and updated Fourth Edition. It provides the entire radiation therapy team(radiation oncologists, medical physicists, dosimetrists, and radiation therapists)with a thorough understanding of the physics and practical clinical applications of advanced radiation therapy technologies, including 3D-CRT, stereotactic radiotherapy, HDR, IMRT, IGRT, and proton beam therapy. These technologies are discussed along with the physical concepts underlying treatment planning, treatment delivery, and dosimetry. This Fourth Edition includes brand-new chapters on image-guided radiation therapy (IGRT) and proton beam therapy. Other chapters have been revised to incorporate the most recent developments in the field. This edition also features more than 100 full-color illustrations throughout. A companion Website will offer the fully searchable text and an image bank.

Principles of Electrical Engineering Materials and Devices has been developed to bridge the gap between traditional electronic circuits texts and semiconductor texts

Contemporary Nonlinear Optics

Solution Manual

Circuit Analysis and Design

Science, Applications and Technology

The Physics of Radiation Therapy

Semiconductor Gas Sensors, Second Edition, summarizes recent research on basic principles, new materials and emerging technologies in this essential field. Chapters cover the foundation of the underlying principles and sensing mechanisms of gas sensors, include expanded content on gas sensing characteristics, such as response, sensitivity and cross-sensitivity, present an overview of the nanomaterials utilized for gas sensing, and review the latest applications for semiconductor gas sensors, including environmental monitoring, indoor monitoring, medical applications, CMOS integration and chemical warfare agents. This second edition has been completely updated, thus ensuring it reflects current literature and the latest materials systems and applications.

Includes an overview of key applications, with new chapters on indoor monitoring and medical applications Reviews developments in gas sensors and sensing methods, including an expanded section on gas sensor theory Discusses the use of nanomaterials in gas sensing, with new chapters on single-layer graphene sensors, graphene oxide sensors, printed sensors, and much more This handbook gives a complete survey of the important topics and results in semiconductor physics. It addresses every fundamental principle and most research topics and areas of application in the field of semiconductor physics. Comprehensive information is provided on crystalline bulk and low-dimensional as well as amorphous semiconductors, including optical, transport, and dynamic properties.

Semiconductor Device Physics and Design teaches readers how to approach device design from the point of view of someone who wants to improve devices and can see the opportunity and challenges. It begins with coverage of basic physics concepts, including the physics behind polar heterostructures and strained heterostructures. The book then details the important devices ranging from p-n diodes to bipolar and field effect devices. By relating device design to device performance and then relating device needs to system use the student can see how device design works in the real world.

Revised and fully updated, the second edition of this graduate textbook offers a comprehensive explanation of the technology and physics of LEDs such as infrared, visible-spectrum, ultraviolet, and white LEDs made from III-V semiconductors. Elementary properties such as electrical and optical characteristics are reviewed, followed by the analysis of advanced device structures. With nine additional chapters, the treatment of LEDs has been vastly expanded, including new material on device packaging, reflectors, UV LEDs, III-V nitride materials, solid-state sources for illumination applications, and junction temperature. Radiative and non-radiative recombination dynamics, methods for improving light extraction, high-efficiency and high-power device designs, white-light emitters with wavelength-converting phosphor materials, optical reflectors, and spontaneous recombination in resonant-cavity structures are discussed in detail. With exercises, solutions, and illustrative examples, this textbook will be of interest to scientists and engineers working on LEDs and graduate students in electrical engineering, applied physics, and materials science.

Principles of Electrical Engineering Materials and Devices

Semiconductor Material and Device Characterization

Physics of Semiconductor Devices

Semiconductor Device Physics and Design

Semiconductor Device Fundamentals

This third edition covers topics in physics as they apply to the life sciences, specifically medicine, physiology, nursing and other applied health fields. It includes many figures, examples and illustrative problems and appendices which provide convenient access to the most important concepts of mechanics, electricity, and optics.

Advances in semiconductor technology have made possible the fabrication of structures whose dimensions are much smaller than the mean free path of an electron. This book gives a thorough account of the theory of electronic transport in such mesoscopic systems. After an initial chapter covering fundamental concepts, the transmission function formalism is presented, and used to describe three key topics in mesoscopic physics: the quantum Hall effect; localisation; and double-barrier tunnelling. Other sections include a discussion of optical analogies to mesoscopic phenomena, and the book concludes with a description of the non-equilibrium Green's function formalism and its relation to the transmission formalism. Complete with problems and solutions, the book will be of great interest to graduate students of mesoscopic physics and nanoelectronic device engineering, as well as to established researchers in these fields.

Principles of Electronic Materials and Devices, Third Edition, is a greatly enhanced version of the highly successful text Principles of Electronic Materials and Devices, Second Edition. It is designed for a first course on electronic materials given in Materials Science and Engineering, Electrical Engineering, and Physics and Engineering Physics Departments at the undergraduate level. The third edition has numerous revisions that include more beautiful illustrations and photographs, additional sections, more solved problems, worked examples, and end-of-chapter problems with direct engineering applications. The revisions have improved the rigor without sacrificing the original semiquantitative approach that both the students and instructors liked and valued. Some of the new end-of-chapter problems have been especially selected to satisfy various professional engineering design requirements for accreditation across international borders. Advanced topics have been collected under Additional Topics, which are not necessary in a short introductory treatment.

A comprehensive introduction and up-to-date reference to SiC power semiconductor devices covering topics from material properties to applications Based on a number of breakthroughs in SiC material science and fabrication technology in the 1980s and 1990s, the first SiC Schottky barrier diodes (SBDs) were released as commercial products in 2001. The SiC SBD market has grown significantly since that time, and SBDs are now used in a variety of power systems, particularly switch-mode power supplies and motor controls. SiC power MOSFETs entered commercial production in 2011, providing rugged, high-efficiency switches for high-frequency power systems. In this wide-ranging book, the authors draw on their considerable experience to present both an introduction to SiC materials, devices, and applications and an in-depth reference for scientists and engineers working in this fast-moving field. Fundamentals of Silicon Carbide Technology covers basic properties of SiC materials, processing technology, theory and analysis of practical devices, and an overview of the most important systems applications. Specifically included are: A complete discussion of SiC material properties, bulk crystal growth, epitaxial growth, device fabrication technology, and characterization techniques. Device physics and operating equations for Schottky diodes, pin diodes, JBS/MP5 diodes, JFETs, MOSFETs, BJTs, IGBTs, and thyristors. A survey of power electronics applications, including switch-mode power supplies, motor drives, power converters for electric vehicles, and converters for renewable energy sources. Coverage of special applications, including microwave devices, high-temperature electronics, and rugged sensors. Fully illustrated throughout, the text is written by recognized experts with over 45 years of combined experience in SiC research and development. This book is intended for graduate students and researchers in crystal growth, material science, and semiconductor device technology. The book is also useful for design engineers, application engineers, and product managers in areas such as power supplies, converter and inverter design, electric vehicle technology, high-temperature electronics, sensors, and smart grid technology.

CMOS

An Introduction

Basic Principles

Semiconductor Devices, Physics and Technology

PHYSICS OF SEMICONDUCTOR DEVICES, 3RD ED

Market_Desc: · **Electrical Engineers Special Features:** · **Over 150 solved examples that clarify concepts are integrated throughout the text.** · **End-of-chapter summary tables and hundreds of figures are included to reinforce the intricacies of modern semiconductor devices**· **Coverage of device optimization issues shows the reader how in each device one has to trade one performance against another** **About The Book: This introductory text presents a well-balanced coverage of semiconductor physics and device operation and shows how devices are optimized for applications. The text begins with an exploration of the basic physical processes upon which all semiconductor devices are based. Next, the author focuses on the operation of the important semiconductor devices along with issues relating to the optimization of device performance.**

This Solution Manual, a companion volume of the book, Fundamentals of Solid-State Electronics, provides the solutions to selected problems listed in the book. Most of the solutions are for the selected problems that had been assigned to the engineering undergraduate students who were taking an introductory device core course using this book. This Solution Manual also contains an extensive appendix which illustrates the application of the fundamentals to solutions of state-of-the-art transistor reliability problems which have been taught to advanced undergraduate and graduate students. This book is also available as a set with Fundamentals of Solid-State Electronics and Fundamentals of Solid-State Electronics — Study Guide.

Neamen's Semiconductor Physics and Devices, Third Edition. deals with the electrical properties and characteristics of semiconductor materials and devices. The goal of this book is to bring together quantum mechanics, the quantum theory of solids, semiconductor material physics, and semiconductor device physics in a clear and understandable way.

The awaited revision of Semiconductor Devices: Physics and Technology offers more than 50% new or revised material that reflects a multitude of important discoveries and advances in device physics and integrated circuit processing. Offering a basic introduction to physical principles of modern semiconductor devices and their advanced fabrication technology, the third edition presents students with theoretical and practical aspects of every step in device characterizations and fabrication, with an emphasis on integrated circuits. Divided into three parts, this text covers the basic properties of semiconductor materials, emphasizing silicon and gallium arsenide; the physics and characteristics of semiconductor devices bipolar, unipolar special microwave and photonic devices; and the latest processing technologies, from crystal growth to lithographic pattern transfer.

Transport Equations for Semiconductors

Semiconductor Physics and Devices

Semiconductor Gas Sensors

Semiconductor Devices

Electronic Transport in Mesoscopic Systems

Market_Desc: · Design Engineers· Research Scientists· Industrial and Electronics Engineering Managers· Graduate Students Special Features: · Completely updated with 30-50% revisions· Will include worked examples and end-of-the-chapter problems (with a solutions manual)· First edition was the most cited work in contemporary engineering and applied science publications (over 12000 citations since 1969) About The Book: This classic reference provides detailed information on the underlying physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. It integrates nearly 1,000 references to important original research papers and review articles, and includes more than 650 high-quality technical illustrations and 25 tables of material parameters for device analysis.

This junior level electronics text provides a foundation for analyzing and designing analog and digital electronics throughout the book. Extensive pedagogical features including numerous design examples, problem solving technique sections, Test Your Understanding questions, and chapter checkpoints lend to this classic text. The author, Don Neamen, has many years experience as an Engineering Educator. His experience shines through each chapter of the book, rich with realistic examples and practical rules of thumb.The Third Edition continues to offer the same hallmark features that made the previous editions such a success.Extensive Pedagogy: A short introduction at the beginning of each chapter links the new chapter to the material presented in previous chapters. The objectives of the chapter are then presented in the Preview section and then are listed in bullet form for easy reference.Test Your Understanding Exercise Problems with provided answers have all been updated. Design Applications are included at the end of chapters. A specific electronic design related to that chapter is presented. The various stages in the design of an electronic thermometer are explained throughout the text.Specific Design Problems and Examples are highlighted throughout as well.

The Third Edition of the standard textbook and reference in the field of semiconductor devices This classic book has set the standard for advanced study and reference in the semiconductor device field. Now completely updated and reorganized to reflect the tremendous advances in device concepts and performance, this Third Edition remains the most detailed and exhaustive single source of information on the most important semiconductor devices. It gives readers immediate access to detailed descriptions of the underlying physics and performance characteristics of all major bipolar, field-effect, microwave, photonic, and sensor devices. Designed for graduate textbook adoptions and reference needs, this new edition includes: A complete update of the latest developments New devices such as three-dimensional MOSFETs, MODFETs, resonant-tunneling diodes, semiconductor sensors, quantum-cascade lasers, single-electron transistors, real-space transfer devices, and more Materials completely reorganized Problem sets at the end of each chapter All figures reproduced at the highest quality Physics of Semiconductor Devices, Third Edition offers engineers, research scientists, faculty, and students a practical basis for understanding the most important devices in use today and for evaluating future device performance and limitations. A Solutions Manual is available from the editorial department.

Contemporary Nonlinear Optics discusses the different activities in the field of nonlinear optics. The book is comprised of 10 chapters. Chapter 1 presents a description of the field of nonlinear guided-wave optics. Chapter 2 surveys a new branch of nonlinear optics under the heading optical solitons. Chapter 3 reviews recent progress in the field of optical phase conjugation. Chapter 4 discusses ultrafast nonlinear optics, a field that is growing rapidly with the ability of generating and controlling femtosecond optical pulses. Chapter 5 examines a branch of nonlinear optics that may be termed nonlinear quantum optics. Chapter 6 reviews the new field of photorefractive adaptive neural networks. Chapter 7 presents a discussion of recent successes in the development of nonlinear optical media based on organic materials. Chapter 8 reviews the field of nonlinear optics in quantum confined structures. Chapter 9 reviews the field of nonlinear laser spectroscopy, with emphasis on advances made during the 1980s. Finally, Chapter 10 reviews the field of nonlinear optical dynamics by considering nonlinear optical systems that exhibit temporal, spatial, or spatio-temporal instabilities. This book is a valuable source for physicists and other scientists interested in optical systems and neural networks.

Materials, Physics, and Devices

Microelectronics

Principles of Electronic Materials and Devices

Fundamentals of Solid-State Electronics

Growth, Characterization, Devices and Applications

Praise for CMOS: Circuit Design, Layout, and SimulationRevised Second Edition from the Technical Reviewers "A refreshing industrial flavor. Design concepts are presented as they are needed for 'just-in-time' learning. Simulating and designing circuits using SPICE is emphasized with literally hundreds of examples. Very few textbooks contain as much detail as this one. Highly recommended!" --Paul M. Furth, New Mexico State University "This book builds a solid knowledge of CMOS circuit design from the ground up. With coverage of process integration, layout, analog and digital models, noise mechanisms, memory circuits, references, amplifiers, PLLs/DLLs, dynamic circuits, and data converters, the text is an excellent reference for both experienced and novice designers alike." --Tyler J. Gomm, Design Engineer, Micron Technology, Inc. "The Second Edition builds upon the success of the first with new chapters that cover additional material such as oversampled converters and non-volatile memories. This is becoming the de facto standard textbook to have on every analog and mixed-signal designer's bookshelf." --Joe Walsh, Design Engineer, AMI Semiconductor CMOS circuits from design to implementation CMOS: Circuit Design, Layout, and Simulation, Revised Second Edition covers the practical design of both analog and digital integrated circuits, offering a vital, contemporary view of a wide range of analog/digital circuit blocks, the BSIM model, data converter architectures, and much more. This edition takes a two-path approach to the topics: design techniques are developed for both long- and short-channel CMOS technologies and then compared. The results are multidimensional explanations that allow readers to gain deep insight into the design process. Features include: Updated materials to reflect CMOS technology's movement into nanometer sizes Discussions on phase- and delay-locked loops, mixed-signal circuits, data converters, and circuit noise More than 1,000 figures, 200 examples, and over 500 end-of-chapter problems In-depth coverage of both analog and digital circuit-level design techniques Real-world process parameters and design rules The book's Web site, CMOSedu.com, provides: solutions to the book's problems; additional homework problems without solutions; SPICE simulation examples using HSPICE, LTspice, and WinSpice; layout tools and examples for actually fabricating a chip; and videos to aid learning

Market_Desc: · Graduate and Advanced Undergraduate Students of Electrical Engineering About The Book: This comprehensive introduction to the elementary theory and properties of semiconductors describes the basic physics of semiconductor materials and technologies for fabrication of semiconductor devices. Addresses approaches to modeling and provides details of measurement techniques. It also includes numerous illustrative examples and graded problems.

Fundamentals of Microelectronics, 2nd Edition is designed to build a strong foundation in both design and analysis of electronic circuits this text offers conceptual understanding and mastery of the material by using modern examples to motivate and prepare readers for advanced courses and their careers. The books unique problem-solving framework enables readers to deconstruct complex problems into components that they are familiar with which builds the confidence and intuitive skills needed for success.

The first edition of "Semiconductor Physics" was published in 1973 by Springer-Verlag Wien-New York as a paperback in the Springer Study Edition. In 1977, a Russian translation by Professor Yu. K. Pozhela and coworkers at Vilnius/USSR was published by Izdatelstvo "MIR", Mo scow. Since then new ideas have been developed in the field of semi conductors such as electron hole droplets, dangling bond saturation in amorphous silicon by hydrogen, or the determination of the fine struc ture constant from surface quantization in inversion layers. New tech niques such as molecular beam epitaxy which has made the realization of the Esaki superlattice possible, deep level transient spectroscopy, and refined a. c. Hall techniques have evolved. Now that the Viennese edition is about to go out of print, Springer-Verlag, Berlin-Heidelberg-New York is giving me the opportunity to include these new subjects in a monograph to appear in the Solid-State Sciences series. Again it has been the intention to cover the field of semiconductor physics comprehensively, although some chapters such as diffusion of hot carriers and their galvanomagnetic phenomena, as well as super conducting degenerate semiconductors and the appendices, had to go for commercial reasons. The emphasis is more on physics than on device as pects.

INTRODUCTION TO SEMICONDUCTOR MATERIALS AND DEVICES

Physics and Technology

Semiconductor Physics And Devices

Physics in Biology and Medicine

Semiconductor Physical Electronics

The new edition of the most detailed and comprehensive single-volume reference on major semiconductor devices The Fourth Edition of Physics of Semiconductor Devices remains the standard reference work on the fundamental physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. This fully updated and expanded edition includes approximately 1,000 references to original research papers and review articles, more than 650 high-quality technical illustrations, and over two dozen tables of material parameters. Divided into five parts, the text first provides a summary of semiconductor properties, covering energy band, carrier concentration, and transport properties. The second part surveys the basic building blocks of semiconductor devices, including p-n junctions, metal-semiconductor contacts, and metal-insulator-semiconductor (MIS) capacitors. Part III examines bipolar transistors, MOSFETs (MOS field-effect transistors), and other field-effect transistors such as JFETs (junction field-effect-transistors) and MESFETs (metal-semiconductor field-effect transistors). Part IV focuses on negative-resistance and power devices. The book concludes with coverage of photonic devices and sensors, including light-emitting diodes (LEDs), solar cells, and various photodetectors and semiconductor sensors. This classic volume, the standard textbook and reference in the field of semiconductor devices: Provides the practical foundation necessary for understanding the devices currently in use and evaluating the performance and limitations of future devices Offers completely updated and revised information that reflects advances in device concepts, performance, and application Features discussions of topics of contemporary interest, such as applications of photonic devices that convert optical energy to electric energy Includes numerous problem sets, real-world examples, tables, figures, and illustrations; several useful appendices; and a detailed solutions manual Explores new work on leading-edge technologies such as MODFETs, resonant-tunneling diodes, quantum-cascade lasers, single-electron transistors, real-space-transfer devices, and MOS-controlled thyristors Physics of Semiconductor Devices, Fourth Edition is an indispensable resource for design engineers, research scientists, industrial and electronics engineering managers, and graduate students in the field.

This junior-level electronics text provides a foundation for analyzing and designing analog and digital electronic circuits. Computer analysis and design are recognized as significant factors in electronics throughout the book. The use of computer tools is presented carefully, alongside the important hand analysis and calculations. The author, Don Neamen, has many years experience as an engineering educator and an engineer. His experience shines through each chapter of the book, rich with realistic examples and practical rules of thumb. The book is divided into three parts. Part 1 covers semiconductor devices and basic circuit applications. Part 2 covers more advanced topics in analog electronics, and Part 3 considers digital electronic circuits.

Physics of Semiconductor Devices covers both basic classic topics such as energy band theory and the gradual-channel model of the MOSFET as well as advanced concepts and devices such as MOSFET short-channel effects, low-dimensional devices and single-electron transistors. Concepts are introduced to the reader in a simple way, often using comparisons to everyday-life experiences such as simple fluid mechanics. They are then explained in depth and mathematical developments are fully described. Physics of Semiconductor Devices contains a list of problems that can be used as homework assignments or can be solved in class to exemplify the theory. Many of these problems make use of Matlab and are aimed at illustrating theoretical concepts in a graphical manner.

Special Features *Computer-based exercises and homework problems -- unique to this text and comprising 25% of the total number of problems -- encourage students to address realistic and challenging problems, experiment with what if scenarios, and easily obtain graphical outputs. Problems are designed to progressively enhance MATLAB-use proficiency, so students need not be familiar with MATLAB at the start of your course. Program scripts that are answers to exercises in the text are available at no charge in electronic form (see Teaching Resources below). *Supplement and Review Mini-Chapters after each of the text's three parts contain an extensive review list of terms, test-like problem sets with answers, and detailed suggestions on supplemental reading to reinforce students' learning and help them prepare for exams. *Read-Only Chapters, strategically placed to provide a change of pace during the course, provide informative, yet enjoyable reading for students. *Measurement Details and Results samples offer students a realistic perspective on the seldom-perfect nature of device characteristics, contrary to the way they are often represented in introductory texts. Content Highlig

Semiconductor Physics

Circuit Design, Layout, and Simulation

Handbook of Deposition Technologies for Films and Coatings

Electronic Circuit Analysis and Design